AMENDMENTS TO THE CLAIMS

- 1. (Currently Amended) A liquid crystal device having a thin film transistor, comprising:
 - a plurality of gate lines formed on a substrate;
- a plurality of data lines insulated from and intersecting said gate lines, said data lines and intersecting gate lines defining a plurality of cells, at least one cell including,
 - a pixel electrode,
- a thin film transistor connected to one of the data lines and one of the gate lines defining the cell,
 - a storage capacitor, and
- a metallic pattern, surrounding the cell, including a drain electrode of the thin film transistor and a storage electrode of the storage capacitor in a single layer and being electrically connected to the pixel electrode, wherein [the] said storage electrode is an upper storage electrode of the storage capacitor, and is formed over the one of the gate lines.
- 2. (Previously Presented) The liquid crystal device of claim 1, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor.

- 3. (Previously Presented) The liquid crystal device of claim 2, further comprising:
- a protective layer disposed between the pixel electrode and the metallic pattern, and wherein
- a portion of a periphery of the pixel electrode overlaps the metallic pattern.
- 4. (Previously Presented) The liquid crystal device of claim 1, further comprising:
- a protective layer disposed between the pixel electrode and the metallic pattern, and wherein
- a portion of a periphery of the pixel electrode overlaps the metallic pattern.
 - 5. (Previously Presented) The liquid crystal device of claim 4, wherein the metallic pattern has an annular shape, and an entire periphery of the pixel electrode overlaps the metallic pattern.

- 6. (Previously Presented) The liquid crystal device of claim 5, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor.
- 7. (Previously Presented) The substrate of claim 1, further comprising:
 a protective layer disposed between the pixel electrode and the metallic
 pattern, and wherein

the pixel electrode is connected to a storage electrode part of the metallic pattern via a first contact hole in the protective layer.

- 8. (Previously Presented) The liquid crystal device of claim 7, wherein the protective layer does not include a contact hole over a drain electrode part of the metallic pattern.
- 9. (Previously Presented) The liquid crystal device of claim 8, wherein the drain electrode part has a greater area than a drain electrode part electrically connected to the pixel electrode via a contact hole in the protective layer over the drain electrode part.

- 10. (Previously Presented) The liquid crystal device of claim 8, wherein the pixel electrode has a larger aspect ratio than if the drain electrode part was electrically connected to the pixel electrode via a contact hole in the protective layer over the drain electrode part.
- 11. (Previously Presented) The liquid crystal device of claim 8, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

12. (Previously Presented) The liquid crystal device of claim 8, wherein the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and

an entire periphery of the pixel electrode overlaps the metallic pattern.

13. (Previously Presented) The liquid crystal device of claim 7, wherein the pixel electrode is connected to a drain electrode part of the metallic pattern via a second contact hole in the protective layer.

14. (Previously Presented) The liquid crystal device of claim 13, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

15. (Previously Presented) The liquid crystal device of claim 13, wherein the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and

an entire periphery of the pixel electrode overlaps the metallic pattern.

16. (Previously Presented) The liquid crystal device of claim 1, further comprising:

a protective layer disposed between the pixel electrode and the metallic pattern, and wherein

the pixel electrode is connected to a drain electrode part of the metallic pattern via a contact hole in the protective layer.

- 17. (Previously Presented) The liquid crystal device of claim 16, wherein the protective layer does not include a contact hole over a storage electrode part of the metallic pattern.
- 18. (Previously Presented) The liquid crystal device of claim 17, wherein the pixel electrode overlaps a gate line, defining the cell but not connected to the thin film transistor, the overlap of the gate line being less than an overlap in a case wherein the protective layer includes a contact hole over a storage electrode part of the metallic pattern.
- 19. (Previously Presented) The liquid crystal device of claim 17, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and
- a portion of a periphery of the pixel electrode overlaps the metallic pattern.
- 20. (Previously Presented) The liquid crystal device of claim 16, wherein the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and

an entire periphery of the pixel electrode overlaps the metallic pattern.

21. (Currently Amended) A liquid crystal device having a thin film transistor, comprising:

a plurality of gate lines formed on a substrate;

a plurality of data lines insulated from and intersecting said gate lines, said data lines and intersecting gate lines defining a plurality of cells, at least one cell including,

a pixel electrode,

a thin film transistor interposed between one of the data lines and the pixel electrode and including a source electrode connected to the one of the data lines, a gate electrode connected to one of the gate lines, a drain electrode, and

a storage capacitor, surrounding the cell, including a storage electrode and a drain electrode in a single layer, the storage capacitor being connected to the pixel electrode, wherein [the] <u>said</u> storage electrode is <u>an upper storage</u> <u>electrode of the storage capacitor and is formed over the one of the gate lines.</u>

22. (Previously Presented) The liquid crystal device of claim 21, wherein the storage electrode and the drain electrode are connected to each other by a metallic pattern.

23. (Currently Amended) A method of manufacturing a thin film transistor substrate, comprising:

forming a gate line having a gate electrode on a transparent substrate; forming a gate insulating layer on the gate electrode;

forming a semiconductor layer on the gate insulating layer;

simultaneously forming a data line having a source electrode, and a metallic pattern including a drain electrode part and a storage electrode part in a single layer, wherein the storage electrode part is an upper storage electrode of a storage capacitor and is formed over the gate line;

forming a protective film over the entire surface; and forming a pixel electrode over the protective film.

24. (Previously Presented) The method of claim 23, wherein the forming the data line and the metallic pattern step is performed simultaneously by forming a conductive layer over the substrate and patterning the conductive layer to form the data line and the metallic pattern such that the metallic pattern is spaced a predetermined distance from the data line.

- 25. (Original) The method of claim 23, wherein the forming a pixel electrode step forms the pixel electrode such that a portion of a periphery of the pixel electrode overlaps the metallic pattern.
- 26. (Original) The method of claim 23, wherein the forming a pixel electrode step forms the pixel electrode such that an entire periphery of the pixel electrode overlaps the metallic pattern.
- 27. (Previously Presented) The method of claim 23, wherein the forming a protective layer step forms the protective layer with a first contact hole exposing the storage electrode part of the metallic pattern.
- 28. (Original) The method of claim 27, wherein the forming a protective layer step does not form the protective layer with a contact hole exposing the drain electrode part of the metallic pattern.
- 29. (Original) The method of claim 27, wherein the forming a protective layer step forms the protective layer with a second contact hole exposing the drain electrode part of the metallic pattern.

- 30. (Original) The method of claim 23, wherein the forming a protective layer step forms the protective layer with a contact hole exposing the drain electrode part of the metallic pattern.
- 31. (Previously Presented) The method of claim 30, wherein the forming a protective layer step does not form the protective layer with a contact hole exposing the storage electrode part of the metallic pattern.